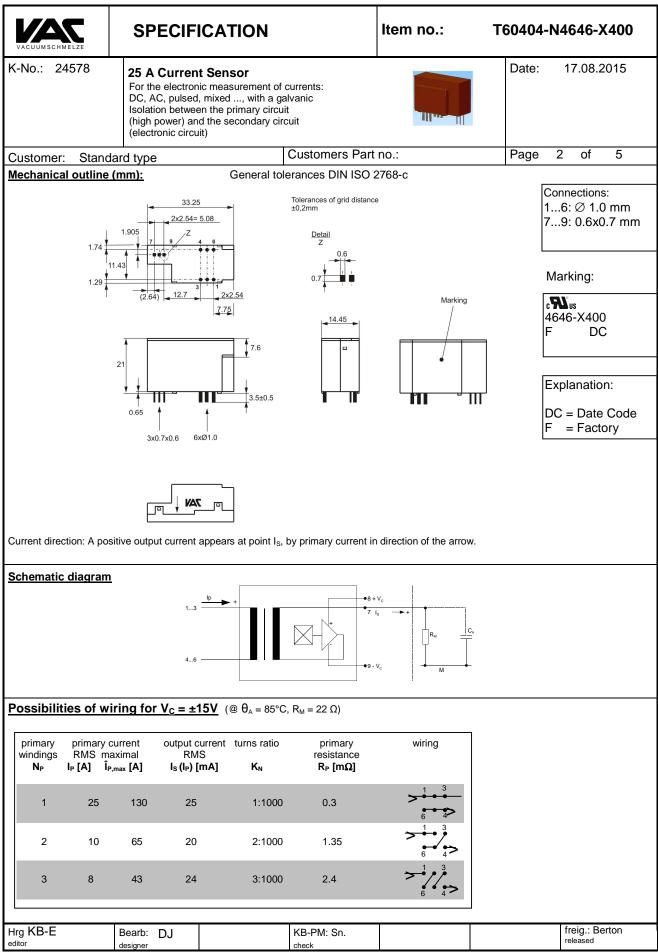
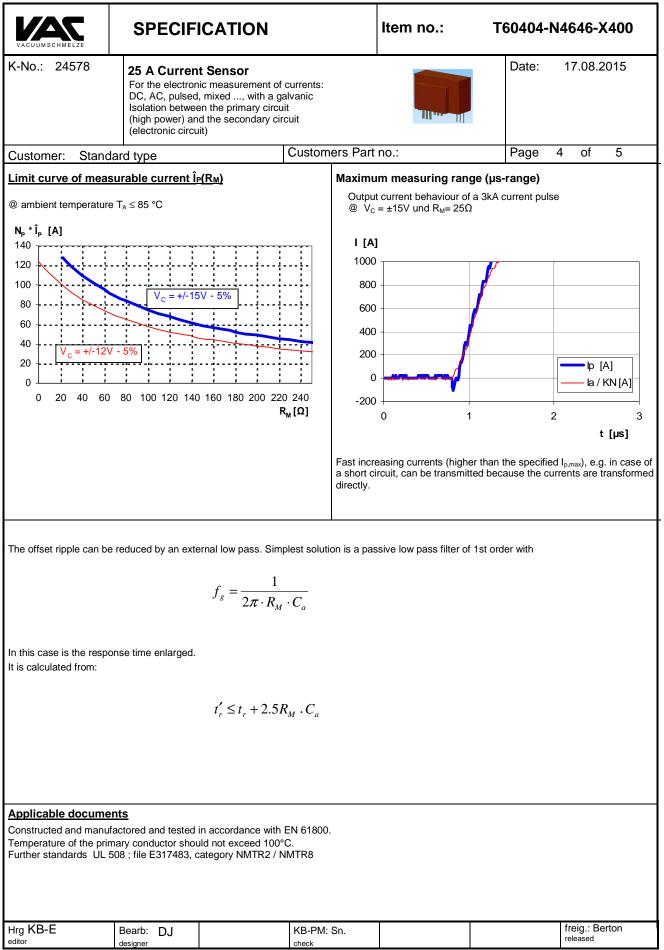
VACUUMSCHMELZE	SPECIFICATION	Ite	m no.:	T60404-N4	4646-X400
K-No.: 24578	<b>25 A Current Sensor</b> For the electronic measurement DC, AC, pulsed, mixed, with a Isolation between the primary cir (high power) and the secondary (electronic circuit)	galvanic cuit		Date:	17.08.2015
Customer: Star	ndard type	Customers Part no.:		Page 1	of 5
Customer:       Standard type       Custom         Description        Characteristics         • Closed loop (compensation) Current Sensor with magnetic field probe       • Excellent accuracy         • Printed circuit board mounting       • Very low offset current         • Casing and materials UL-listed       • Very low temperature depen current drift         • Very low hysteresis of offset       • Low response time         • Wide frequency bandwidth       • Compact design         • Reduced offset ripple       • Reduced offset ripple		urrent ature dependency and offset sis of offset current ne pandwidth	Applications           Mainly used for stationary operation in ir applications:           ency and offset         • AC variable speed drives and serv drives		
Electrical data – I	Ratings				
I <sub>PN</sub>	Primary nominal r.m.s. current			25	А
R <sub>M</sub>	Measuring resistance $V_c=\pm 12$			10 200	Ω
	V <sub>C</sub> =± 1			22 400	Ω
I <sub>SN</sub> Kn	Secondary nominal r.m.s. curr Turns ratio	ent		25 13 : 1000	mA
<u> Accuracy – Dyna</u>	mic performance data	min	. typ.	max.	Unit
I <sub>P,max</sub>	Max. measuring range		. typ.	max.	Unit
	@ $V_{C} = \pm 12V$ , $R_{M} = 10 \Omega$ ( $t_{max}$		0		А
X	@ $V_{C} = \pm 15V$ , $R_{M} = 22 \Omega$ ( $t_{max}$	= 10sec) ±13	-		A
Х	Accuracy @ $I_{PN}$ , $\theta_A = 25^{\circ}C$		0.1	0.5	%
εL	Linearity	500	0.00	0.1	%
l <sub>0</sub>	Offset current @ I <sub>P</sub> =0A, $\theta_A = 2$	25°C	0.02	0.1	mA
t <sub>r</sub>	Response time	· -	500		ns
t <sub>ra</sub> f <sub>BW</sub>	Reaction time at di/dt = 100 A/ Frequency bandwidth	-	200		ns kHz
General data					KI Z
		min	. typ.	max.	Unit
$\vartheta_{A}$	Ambient operating temperatur	e -40		+85	°C
ϑs	Ambient storage temperature	-40		+90	°C
m	Mass		12		g
Vc	Supply voltage	±11		15 ±15.75	V
l <sub>c</sub>	Current consumption		18,5		mA
*S <sub>clear</sub>	clearance (component without so	1 /			mm
*S <sub>creep</sub> *U <sub>sys</sub>	creepage (component without so System voltage	Ider pad) 10.2		600	mm V <sub>RMS</sub>
*U <sub>AC</sub>	Working voltage			1020	VRMS
*U <sub>PD</sub>	Rated discharge voltage			1400	Vs
	Max. potential difference acc.	to UL 508		600	V <sub>AC</sub>
	manufactored and tested in accord ion, Insulation material group 1, Po			in 7 – 9)	
Date Name	Isuue Amendment				
17.08.15 DJ	82 Marking of item-no, value of p				5-420
17.04.13 KRe.	82 Mechanical outline: marking w				
Hrg KB-E	Boorby D.L	KB-PM: Sn.			freig.: Berton
	Bearb: DJ	ND-PIVI. SII.			released



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VACUUMSCHMELZE	SPECI	FICATION	Item no.:	T60404-	N4646-X400
K-No.: 2457	For the electr DC, AC, puls Isolation betw	ent Sensor onic measurement of currents: ed, mixed, with a galvanic veen the primary circuit and the secondary circuit cuit)		Date:	17.08.2015
Customer: S	standard type	Customers	s Part no.:	Page	3 of 5
Electrical Data	(investigate by a type che	cking)			
V <sub>Ctot</sub>	Maximum su	pply voltage (without function)	<mark>min. typ.</mark>	<b>max.</b> ±18	Unit V
V Ctot		8 V: for 1s per hour		10	v
Rs	Secondary c	oil resistance @ $\theta_A=85^{\circ}C$		88	Ω
R <sub>p</sub>	Primary coil ı	esistance per turn @ T <sub>A</sub> =25°C		1	mΩ
X <sub>Ti</sub>	Temperature	drift of X @ $\vartheta_A$ = -40 +85 °C		0.1	%
I <sub>0ges</sub>		t (including I <sub>0</sub> , I <sub>0t</sub> , I <sub>0T</sub> )		0.15	mA
l <sub>Ot</sub>		ift Offset current I <sub>0</sub>	0.05		mA
I <sub>OT</sub>		t temperature drift $I_0 @ \vartheta_A = -40$			mA
I <sub>OH</sub>		rent @ I <sub>P</sub> =0 (caused by primary c	urrent 3 x I <sub>PN</sub> ) 0.04		mA
$\Delta I_0 / \Delta V_C$		ge rejection ratio		0.01	mA/V
l <sub>oss</sub>		(with1 MHz- filter first order)	0.00	0,15	mA
l <sub>oss</sub>		(with 100 kHz- filter first order)	0.03		mA
i <sub>oss</sub> C <sub>k</sub>		(with 20 kHz- filter first order) ssible coupling capacity (primar		0.015	mA pF
<b>U</b> k			y – secondary) 4		μr
		Stress according to M3209/3 - 2000 Hz, 1 min/Oktave, 2 hou	rs	10g	
			rs	10g	
	Settings: 10 -	- 2000 Hz, 1 min/Oktave, 2 hou	om temperature)		
$K_N(N_1/N_2)$	Settings: 10 - easurement after tempe (V) M3011/6	– 2000 Hz, 1 min/Oktave, 2 hou prature balance of the samples at ro Transformation ratio (I <sub>P</sub>	om temperature)	13 : 100	00±0.5 %
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub>	Settings: 10 - easurement after temper (V) M3011/6 (V) M3226	– 2000 Hz, 1 min/Oktave, 2 hou erature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current	om temperature)	13 : 100 < 0.1	mA
$K_N(N_1/N_2)$	Settings: 10 - easurement after tempe (V) M3011/6	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s	om temperature)	13 : 100	
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014	– 2000 Hz, 1 min/Oktave, 2 hou erature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current	om temperature) ⊳=3*10A, 40-80 Hz)	13 : 100 < 0.1	mA
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <sup>2</sup>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltage	om temperature) ⊳=3*10A, 40-80 Hz)	13 : 100 < 0.1 2.5 1300	mA kV V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <sup>2</sup>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9)	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltage	om temperature) ⊳=3*10A, 40-80 Hz) ge acc. M3024 (RMS)	13 : 100 < 0.1 2.5 1300	mA kV V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <sup>2</sup>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064)	om temperature) ⊳=3*10A, 40-80 Hz) ge acc. M3024 (RMS)	13 : 100 < 0.1 2.5 1300	mA kV V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL Type Testing ( Designed acc V <sub>W</sub>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient (1.2 µs / 50 µ	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064) Is-wave form)	om temperature) s=3*10A, 40-80 Hz) ge acc. M3024 (RMS) material group 1	13 : 100 < 0.1 2.5 1300 1625 8	mA kV V V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <sup>2</sup> <b>Type Testing</b> ( Designed acc	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient (1.2 µs / 50 µ Testing volta	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064)	om temperature) ==3*10A, 40-80 Hz) ge acc. M3024 (RMS) material group 1 (5 s)	13 : 100 < 0.1 2.5 1300 1625 8 8 5 1500	mA kV V V kV V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL / T <b>ype Testing</b> ( Designed acc V <sub>W</sub> V <sub>d</sub>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient (1.2 µs / 50 µ Testing volta	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064) Is-wave form) ge acc. M3014 (RMS) arge voltage acc. M3024 (RMS)	om temperature) ==3*10A, 40-80 Hz) ge acc. M3024 (RMS) material group 1 (5 s)	13 : 100 < 0.1 2.5 1300 1625 8 8	mA kV V V kV
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <b>Type Testing</b> ( Designed acc V <sub>W</sub> V <sub>d</sub>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient (1.2 µs / 50 µ Testing volta Partial discha	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064) Is-wave form) ge acc. M3014 (RMS) arge voltage acc. M3024 (RMS)	om temperature) ==3*10A, 40-80 Hz) ge acc. M3024 (RMS) material group 1 (5 s)	13 : 100 < 0.1 2.5 1300 1625 8 8 5 1500	mA kV V V kV V
K <sub>N</sub> (N <sub>1</sub> /N <sub>2</sub> ) I <sub>0</sub> V <sub>P,eff</sub> V <sub>e</sub> (AQL <b>Type Testing</b> ( Designed acc V <sub>W</sub> V <sub>d</sub>	Settings: 10 - easurement after tempe (V) M3011/6 (V) M3226 (V) M3014 I/S4) Pin 1 - 6 to Pin 7 – 9) ording standard EN 6 HV transient (1.2 µs / 50 µ Testing volta Partial discha	- 2000 Hz, 1 min/Oktave, 2 hou rature balance of the samples at ro Transformation ratio (I <sub>P</sub> Offset current Test voltage, rms, 1s Pin 1 - 6 to Pin 7 - 9 Partial discharge voltag with V <sub>vor</sub> (RMS) 51800-5-1:2007 with insulation r test according (to M3064) Is-wave form) ge acc. M3014 (RMS) arge voltage acc. M3024 (RMS)	om temperature) ==3*10A, 40-80 Hz) ge acc. M3024 (RMS) material group 1 (5 s)	13 : 100 < 0.1 2.5 1300 1625 8 8 5 1500	mA kV V V kV V

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VACUUMSCH	IELZE	SPECIFIC	ATION	Item no.:	T60404-N4646-X400
K-No.: 24	4578		easurement of currents: ed, with a galvanic e primary circuit		Date: 17.08.2015
Customer:	Stand	ard type	Custome	rs Part no.:	Page 5 of 5
I <sub>он</sub> : I <sub>ot</sub> :	Long ter	m drift of $I_o$ after 100 t	temperature cycles in the	-	
t <sub>r</sub> :	at $I_P = 0$ .	9 I <sub>Pmax</sub> between a r	ectangular current and t	he output current.	ent range), measured as delay time
∆t (I <sub>Pmax</sub> ):				e rapid current pulse rate e a primary current rise of	
X <sub>ges</sub> (I <sub>PN</sub> ):		$\begin{array}{l} \text{of all possible errors} \\ 00 \cdot \left  \frac{I_{\text{s}}(I_{\text{PN}})}{K_{\text{N}} \cdot I_{\text{SN}}} - 1 \right  \% \end{array}$		ange by measuring a curre	ent I <sub>PN</sub> :
X:	X =10	$0 \cdot \left  \begin{array}{c} \frac{I_{SB}}{I_{SN}} - 1 \right  \%$	or in the final inspection		
X <sub>Ti</sub> :	Tempera obtained	ature drift of the rated	value orientated output	-	as the (positive) rated current ( $I_0 = 0$ in a specified temperature range,
	(I <sub>SB</sub> : Sec	ondary current $\theta_{A1}$ or			
ε <sub>L</sub> :			$ \varepsilon_{\rm L} = 100 \cdot \left  \frac{I_{\rm P}}{I_{\rm PN}} - \frac{I_{\rm Sx}}{I_{\rm SN}} \right  $ Is the corresponding of		
Hrg KB-E		Bearb: DJ	KB-PM: S	'n.	freig.: Berton released

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